WHAT IS CLAIMED IS:

1. A wafer producing method for producing a wafer from a hexagonal single crystal ingot, the wafer producing method comprising:

a planarization step of planarizing an upper surface of the hexagonal single crystal ingot;

a first production history forming step of applying a laser beam of such a wavelength as to be transmitted through the hexagonal single crystal ingot to the hexagonal single crystal ingot, with a focal point of the laser beam positioned in an inside of a region not to be formed with devices of a wafer to be produced secondly, from the upper surface of the hexagonal single crystal ingot which has been planarized, to form a production history;

an exfoliation layer forming step of applying a laser beam of such a wavelength as to be transmitted through the hexagonal single crystal ingot to the hexagonal single crystal ingot, with a focal point of the laser beam positioned at a depth corresponding to a wafer to be produced firstly, from the upper surface of the hexagonal single crystal ingot which has been planarized, to form an exfoliation layer;

a second production history forming step of

applying a laser beam of such a wavelength as to be transmitted through the hexagonal single crystal ingot to the hexagonal single crystal ingot, with a focal point of the laser beam positioned in an inside of a region not to be formed with devices of the wafer to be produced firstly, from the upper surface of the hexagonal single crystal ingot which has been planarized, to form a production history; and

a wafer exfoliation step of exfoliating the wafer to be produced firstly from the hexagonal single crystal ingot, with the exfoliation layer as a starting point of exfoliation, to produce a wafer,

wherein the planarization step, the first production history forming step, the exfoliation layer forming step, and the wafer exfoliation step are repeated.

2. The wafer producing method according to claim 1,

wherein the production histories formed in the first production history forming step and the second production history forming step include any one of a lot number of the hexagonal single crystal ingot, an order of the wafer produced, a production date of the wafer, a production plant of the wafer, and a machine model that has contributed to the production of the wafer.

3. The wafer producing method according to claim 1,

wherein the hexagonal single crystal ingot is a hexagonal single crystal SiC ingot having a first surface, a second surface opposite to the first surface, a c-axis extending from the first surface to the second surface, and a c-plane orthogonal to the c-axis, with the c-axis being inclined relative to a perpendicular to the first surface, and with an off angle being formed by the c-plane and the first surface, and

in the exfoliation layer forming step,

a pulsed laser beam of such a wavelength as to be transmitted through the hexagonal single crystal SiC ingot is applied to the hexagonal single crystal SiC ingot, with a focal point of the pulsed laser beam positioned at a depth corresponding to a thickness of a wafer to be produced from the first surface, and with the hexagonal single crystal SiC ingot and the focal point being relatively moved in a first direction orthogonal to a second direction in which the off angle is formed, to cause SiC to be separated into Si and C, to cause the pulsed laser beam applied next to be absorbed in previously formed C, and to cause SiC to be separated into Si and C in a chain reaction manner, thereby forming a rectilinear modified layer and forming a crack extending from the modified layer along the c-plane, and

the hexagonal single crystal SiC ingot and the focal point are relatively moved in the direction in which the off angle is formed, to perform indexing by a predetermined amount, thereby forming the exfoliation layer.